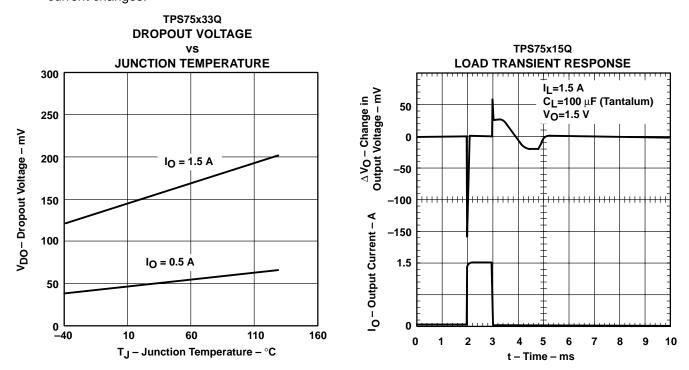
- 1.5-A Low-Dropout Voltage Regulator
- Available in 1.5-V, 1.8-V, 2.5-V, 3.3-V, Fixed Output and Adjustable Versions
- Open Drain Power-Good (PG) Status Output (TPS751xxQ)
- Open Drain Power-On Reset With 100-ms Delay (TPS753xxQ)
- Dropout Voltage Typically 160 mV at 1.5 A (TPS75133Q)
- Ultralow 75 μA Typical Quiescent Current
- Fast Transient Response
- 2% Tolerance Over Specified Conditions For Fixed-Output Versions
- 20-Pin TSSOP (PWP) PowerPAD[™] Package
- Thermal Shutdown Protection

description

The TPS753xxQ and TPS751xxQ are low dropout regulators with integrated power-on reset and power-good (PG) functions respectively. These devices are capable of supplying 1.5 A of output current with a dropout of 160 mV (TPS75133Q, TPS75333Q). Quiescent current is 75 μ A at full load and drops down to 1 μ A when the device is disabled. TPS751xxQ and TPS753xxQ are designed to have fast transient response for larger load current changes.





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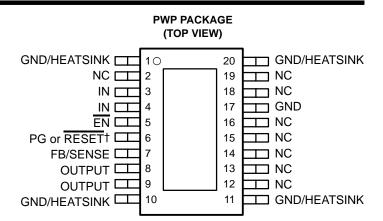
PowerPAD is a trademark of Texas Instruments.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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1



NC - No internal connection

[†] PG is on the TPS751xx and RESET is on the TPS753xx

SLVS241B - MARCH 2000 - REVISED JUNE 2003

description (continued)

Because the PMOS device behaves as a low-value resistor, the dropout voltage is very low (typically 160 mV at an output current of 1.5 A for the TPS75x33Q) and is directly proportional to the output current. Additionally, since the PMOS pass element is a voltage-driven device, the guiescent current is very low and independent of output loading (typically 75 µA over the full range of output current, 1 mA to 1.5 A). These two key specifications yield a significant improvement in operating life for battery-powered systems.

The device is enabled when EN is connected to a low level voltage. This LDO family also features a sleep mode; applying a TTL high signal to EN (enable) shuts down the regulator, reducing the quiescent current to less than 1 μ A at T_{.1} = 25°C.

For the TPS751xxQ, the power-good terminal (PG) is an active high, open drain output, which can be used to implement a power-on reset or a low-battery indicator.

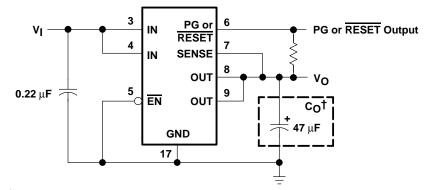
The RESET (SVS, POR, or power on reset) output of the TPS753xxQ initiates a reset in microcomputer and microprocessor systems in the event of an undervoltage condition. An internal comparator in the TPS753xxQ monitors the output voltage of the regulator to detect an undervoltage condition on the regulated output voltage. When the output reaches 95% of its regulated voltage, RESET goes to a high-impedance state after a 100-ms delay. RESET goes to a logic-low state when the regulated output voltage is pulled below 95% (i.e., over load condition) of its regulated voltage.

The TPS751xxQ or TPS753xxQ is offered in 1.5-V, 1.8-V, 2.5-V and 3.3-V fixed-voltage versions and in an adjustable version (programmable over the range of 1.5 V to 5 V). Output voltage tolerance is specified as a maximum of 2% over line, load, and temperature ranges. The TPS751xxQ and TPS753xxQ families are available in 20-pin TSSOP (PWP) packages.

т.	OUTPUT VOLTAGE	TSSOP (PWP)			
Тj	(TYP)	PG	RESET		
	3.3 V	TPS75133QPWP	TPS75333QPWP		
	2.5 V	TPS75125QPWP	TPS75325QPWP		
-40°C to 125°C	1.8 V	TPS75118QPWP	TPS75318QPWP		
	1.5 V	TPS75115QPWP	TPS75315QPWP		
	Adjustable 1.5 V to 5 V	TPS75101QPWP	TPS75301QPWP		

AVAILABLE OPTIONS

NOTE: The TPS75x01 is programmable using an external resistor divider (see application information). The PWP package is available taped and reeled. Add an R suffix to the device type (e.g., TPS75201QPWPR) to indicate tape and reel.

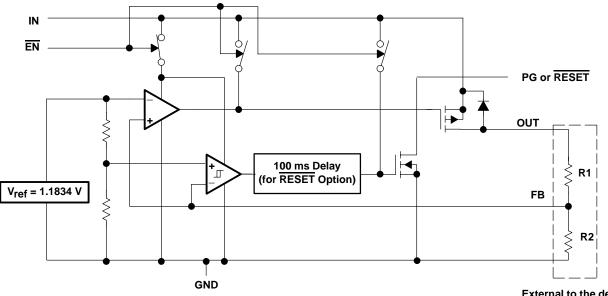


[†] See application information section for capacitor selection details.

Figure 1. Typical Application Configuration (For Fixed Output Options)

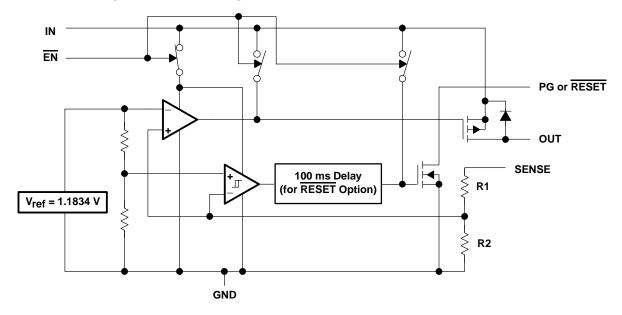


functional block diagram—adjustable version



External to the device

functional block diagram—fixed-voltage version





Terminal Functions (TPS751xxQ)

TERMI	NAL	1/0	DESCRIPTION
NAME	NO.	10	DESCRIPTION
EN	5	Ι	Enable Input
FB/SENSE	7	I	Feedback input voltage for adjustable device (sense input for fixed options)
GND	17		Regulator Ground
GND/HEATSINK	1, 10, 11, 20		Ground/heatsink
IN	3, 4	I	Input voltage
NC	2, 12, 13, 14, 15, 16, 18, 19		No connection
OUTPUT	8, 9	0	Regulated output voltage
PG	6	0	Power good output

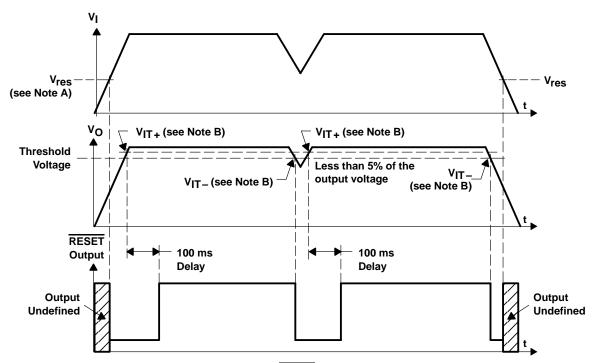
Terminal Functions (TPS753xxQ)

TERMI	NAL	I/O	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
EN	5	I	Enable Input
FB/SENSE	7	I	Feedback input voltage for adjustable device (sense input for fixed options)
GND	17		Regulator Ground
GND/HEATSINK	1, 10, 11, 20		Ground/heatsink
IN	3, 4	I	Input voltage
NC	2, 12, 13, 14, 15, 16, 18, 19		No connection
OUTPUT	8, 9	0	Regulated output voltage
RESET	6	0	Reset output



SLVS241B - MARCH 2000 - REVISED JUNE 2003

TPS753xxQ RESET timing diagram

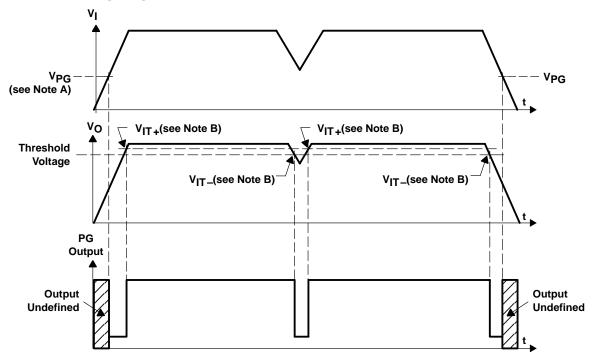


NOTES: A. Vres is the minimum input voltage for a valid RESET. The symbol Vres is not currently listed within EIA or JEDEC standards for semiconductor symbology.

B. VIT –Trip voltage is typically 5% lower than the output voltage (95%V_O) V_{IT}– to V_{IT+} is the hysteresis voltage.



TPS751xxQ PG timing diagram



- NOTES: A. VPG is the minimum input voltage for a valid PG. The symbol VPG is not currently listed within EIA or JEDEC standards for semiconductor symbology.
 - B. VIT Trip voltage is typically 17% lower than the output voltage (83%VO) VIT- to VIT+ is the hysteresis voltage.



SLVS241B - MARCH 2000 - REVISED JUNE 2003

absolute maximum ratings over operating junction temperature range (unless otherwise noted)[†]

Input voltage range [‡] , V _I	–0.3 V to 6.0 V
Voltage range at EN	
Maximum PG voltage (TPS751xxQ)	16.5 V
Maximum RESET voltage (TPS753xxQ)	16.5 V
Peak output current	Internally limited
Continuous total power dissipation	See dissipation rating tables
$O_{\rm U}$ to $U_{\rm U}$ (OUTDUT ED)	
Output voltage, V _O (OUTPUT, FB)	5.5 V
Operating virtual junction temperature range, T_J	
	40°C to 125°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

[‡] All voltage values are with respect to network terminal ground.

DISSIPATION RATING TABLE 1 – FREE-AIR TEMPERATURES									
PACKAGE	AIR FLOW (CFM)	T _A < 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING				
PWP§	0	2.9 W	23.5 mW/°C	1.9 W	1.5 W				
PWP3	300	4.3 W	34.6 mW/°C	2.8 W	2.2 W				
PWP¶	0	3 W	23.8 mW/°C	1.9 W	1.5 W				
PVVP	300	7.2 W	57.9 mW/°C	4.6 W	3.8 W				

§ This parameter is measured with the recommended copper heat sink pattern on a 1-layer PCB, 5-in × 5-in PCB, 1 oz. copper, 2-in \times 2-in coverage (4 in²).

This parameter is measured with the recommended copper heat sink pattern on a 8-layer PCB, 1.5-in × 2-in PCB, 1 oz. copper with layers 1, 2, 4, 5, 7, and 8 at 5% coverage (0.9 in²) and layers 3 and 6 at 100% coverage (6 in²). For more information, refer to TI technical brief SLMA002.

recommended operating conditions

	MIN	MAX	UNIT
Input voltage, VI#	2.7	5.5	V
Output voltage range, VO	1.5	5	V
Output current, IO	0	1.5	А
Operating virtual junction temperature, TJ	-40	125	°C

[#] To calculate the minimum input voltage for your maximum output current, use the following equation: V_{I(min)} = V_{O(max)} + V_{DO(max load)}.



electrical characteristics over recommended operating junction temperature range ($T_J = -40^{\circ}C$ to 125°C), $V_I = V_{O(typ)} + 1 V$, $I_O = 1 \text{ mA}$, EN = 0 V, $C_o = 47 \mu F$ (unless otherwise noted)

PARAMETER		TEST C	CONDITIONS	MIN	TYP	MAX	UNIT			
		Adjustable	$1.5 \text{ V} \le \text{V}_{\text{O}} \le 5.5 \text{ V},$	TJ = 25°C		Vo				
		Voltage	$1.5 \text{ V} \le \text{V}_0 \le 5.5 \text{ V}$		0.98 VO		1.02 V _O			
		1510	TJ = 25°C,	2.7 V < V _{IN} < 5.5 V		1.5				
		1.5 V Output	2.7 V < V _{IN} < 5.5 V		1.470		1.530			
Output voltage (see Notes 1 and 3)		T _J = 25°C,	2.8 V < V _{IN} < 5.5 V		1.8					
	1.8 V Output	2.8 V < V _{IN} < 5.5 V		1.764		1.836	V			
		TJ = 25°C,	3.5 V < V _{IN} < 5.5 V		2.5					
		2.5 V Output	3.5 V < V _{IN} < 5.5 V		2.450		2.550			
			TJ = 25°C,	4.3 V < V _{IN} < 5.5 V		3.3				
		3.3 V Output	4.3 V < V _{IN} < 5.5 V		3.234		3.366			
Ouissesst sur		(and Nate 2)	T _J = 25°C,	See Note 3		75		1		
Quiescent curr	ent (GND current)	(see Note 2)	See Note 3				125	μA		
Output voltage line regulation $(\Delta V_O/V_O)$ (see Notes 1 and 2) Output voltage line regulation $(\Delta V_O/V_O)$ (see Notes 1 and 2)		$V_{O} + 1 V < V_{I} \le 5.5 V_{O}$		0.01		%/V				
		V _O + 1 V < V _I < 5.5 \			0.1	70/ V				
Load regulation	n (see Note 3)					1		mV		
Output noise v	oltage		BW = 300 Hz to 50 k C _O = 100 μ F,	Hz, V _O = 1.5 V T _J = 25°C		60		μVrms		
Output current	Limit		V _O = 0 V			3.3	4.5	А		
Thermal shutde	own junction tempe	erature				150		°C		
o			$\overline{\text{EN}} = V_{I_1}$	TJ = 25°C,		1		μA		
Standby currer	nt		$\overline{EN} = V_{I}$				10	μA		
FB input currer	nt	TPS75x01Q	FB = 1.5 V		-1		1	μΑ		
High level enab	ole input voltage	-			2			V		
Low level enab	ole input voltage						0.7	V		
Power supply r	ipple rejection (see	e Note 2)	f = 100 Hz, TJ = 25°C,	C _O = 100 μF, See Note 1, I _O = 1.5 A		63		dB		
	Minimum input voltage for valid PG Trip threshold voltage Hysteresis voltage		I _{O(PG)} = 300μA,	$V(PG) \le 0.8 V$		1	1.3	V		
PG			VO decreasing		80		86	%Vo		
(TPS751xxQ)			Measured at VO			0.5		%Vo		
. ,	Output low voltage		V _I = 2.7 V,	I _{O(PG)} = 1mA		0.15	0.4	V		
	Leakage current	-	V _(PG) = 5.5 V		<u> </u>		1	μA		

NOTES: 1. Minimum IN operating voltage is 2.7 V or $V_{O(typ)}$ + 1 V, whichever is greater. Maximum IN voltage 5.5 V. 2. If $V_O \le 1.8$ V then $V_{imin} = 2.7$ V, $V_{imax} = 5.5$ V:

Line Reg. (mV) =
$$(\%/V) \times \frac{V_O(V_{imax} - 2.7 V)}{100} \times 1000$$

If $V_O \ge 2.5$ V then $V_{imin} = V_O + 1$ V, $V_{imax} = 5.5$ V:

Line Reg. (mV) =
$$(\%/V) \times \frac{V_O(V_{imax} - (V_O + 1 V))}{100} \times 1000$$

7

N

3. $I_0 = 1 \text{ mA to } 1.5 \text{ A}$



electrical characteristics over recommended operating junction temperature range (T_J = -40°C to 125°C), V_I = V_{O(typ)} + 1 V, I_O = 1 mA, EN = 0 V, C_o = 47 μ F (unless otherwise noted) (continued)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Minimum input voltage for valid RESET	$I_{O}(RESET) = 300 \ \mu A, V_{(RESET)} \le 0.8 \ V$		1.1	1.3	V
Reset	Trip threshold voltage	VO decreasing	92		98	%VO
	Hysteresis voltage	Measured at V_O		0.5		%VO
(TPS753xxQ)	Output low voltage	IO(RESET) = 1 mA		0.15	0.4	V
	Leakage current	$V_{(RESET)} = 5.5 V$			1	μA
	RESET time-out delay			100		ms
Input ourreat ($\overline{EN} = V_{I}$	-1		1	μA
Input current (E	=1N)	<u>EN</u> = 0 V	-1	0	1	μA
High level EN i	nput voltage		2			V
Low level EN input voltage					0.7	V
Dropout voltage, (3.3 V output) (see Note 4)		$I_{O} = 1.5 \text{ A},$ $V_{I} = 3.2 \text{ V},$ $T_{J} = 25^{\circ}\text{C}$		160		mV
-		I _O = 1.5 A, V _I = 3.2 V			300	

NOTE 4: IN voltage equals V_O(Typ) - 100 mV; TPS75x15Q, TPS75x18Q and TPS75x25Q dropout voltage limited by input voltage range limitations (i.e., TPS75x33Q input voltage needs to drop to 3.2 V for purpose of this test).

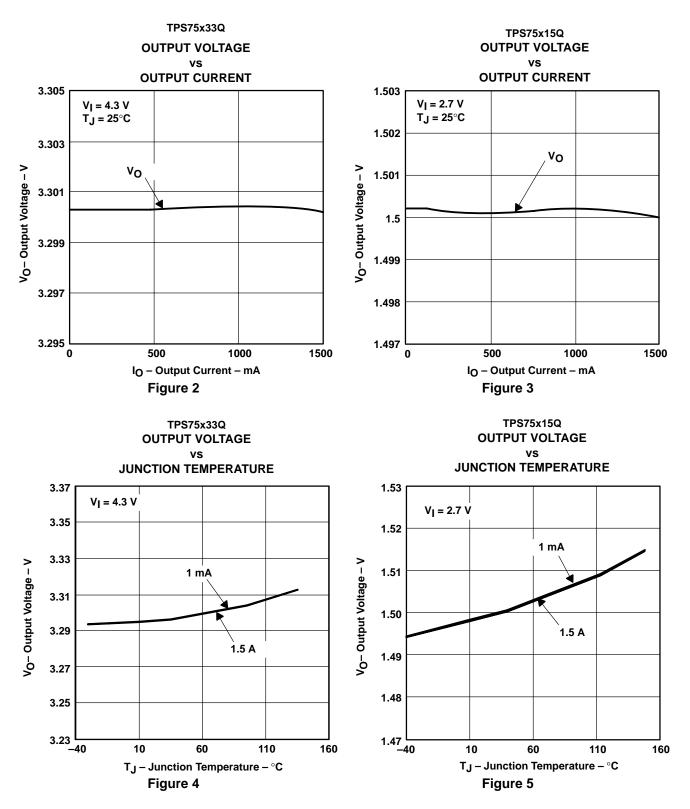
			FIGURE
Vo	Outputuelteere	vs Output current	2, 3
VO	Output voltage	vs Junction temperature	4, 5
	Ground current	vs Junction temperature	6
	Power supply ripple rejection	vs Frequency	7
	Output spectral noise density	vs Frequency	8
Z ₀	Output impedance	vs Frequency	9
\/	Dreamentuskana	vs Input voltage	10
VDO	Dropout voltage	vs Junction temperature	11
	Input voltage (min)	vs Output voltage	12
	Line transient response		13, 15
	Load transient response		14, 16
VO	Output voltage	vs Time	17
	Equivalent series resistance (ESR)	vs Output current	19, 20

Table of Graphs



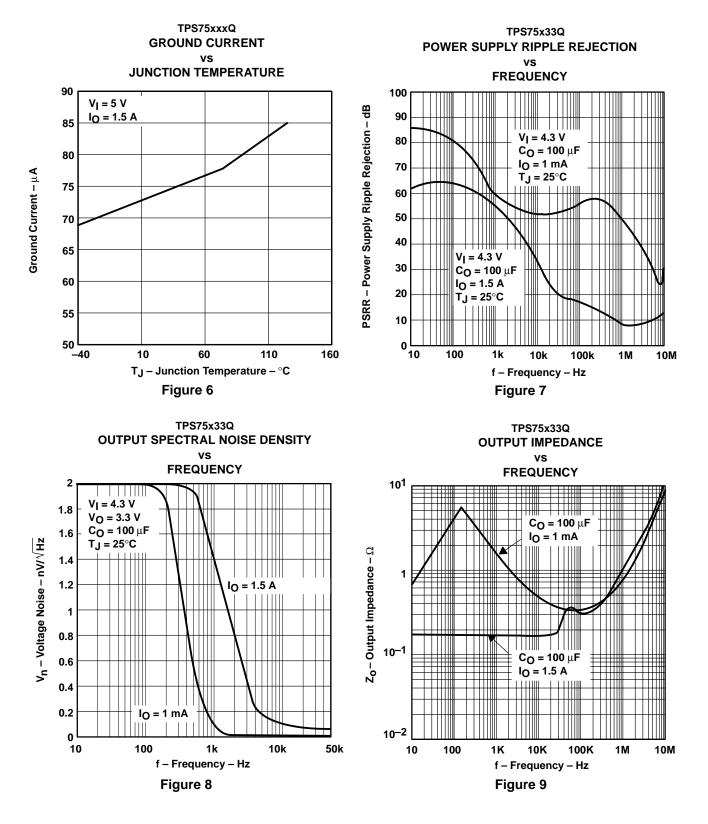
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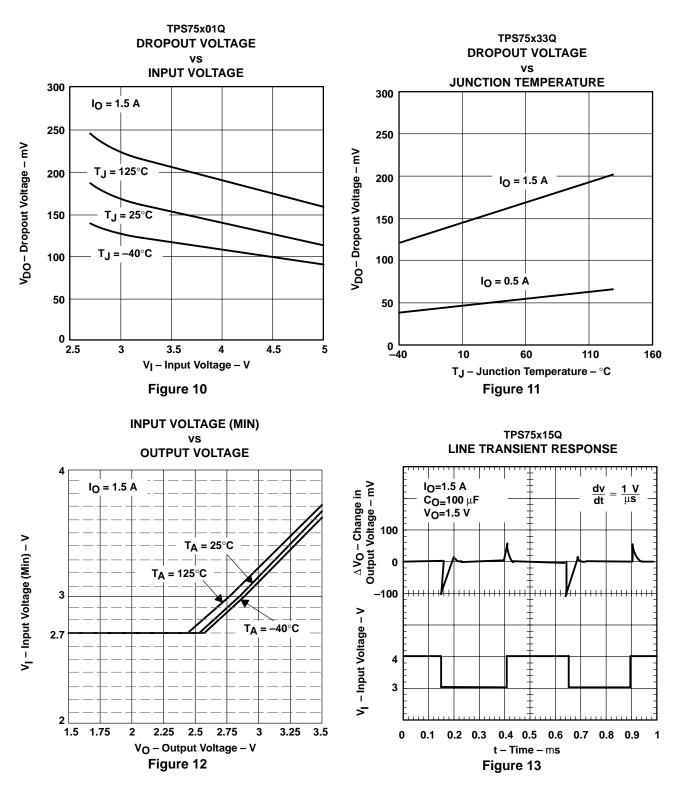
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TYPICAL CHARACTERISTICS



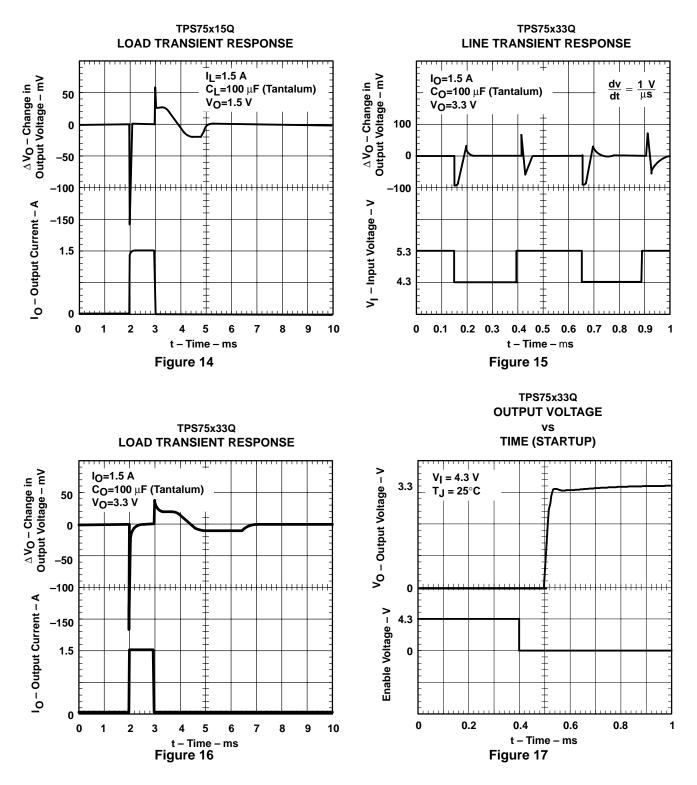
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TYPICAL CHARACTERISTICS



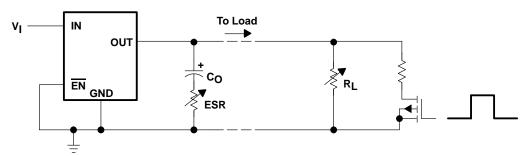
TYPICAL CHARACTERISTICS



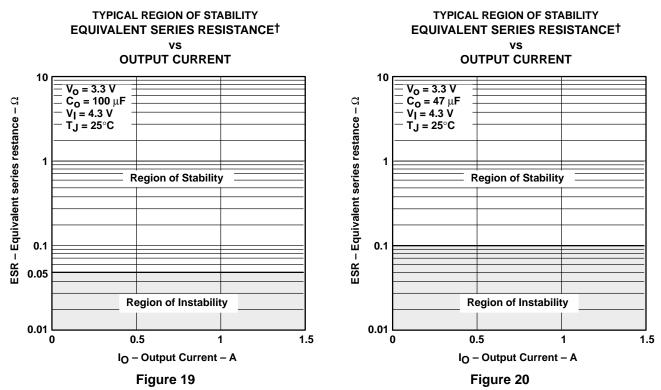


SLVS241B - MARCH 2000 - REVISED JUNE 2003

TYPICAL CHARACTERISTICS







† Equivalent series resistance (ESR) refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to Co.



SLVS241B - MARCH 2000 - REVISED JUNE 2003

APPLICATION INFORMATION

The TPS751xxQ or TPS753xxQ family includes four fixed-output voltage regulators (1.5 V, 1.8 V, 2.5 V and 3.3 V), and an adjustable regulator, the TPS75x01Q (adjustable from 1.5 V to 5 V).

minimum load requirements

The TPS751xxQ and TPS753xxQ families are stable even at no load; no minimum load is required for operation.

pin functions

enable (EN)

The EN terminal is an input which enables or shuts down the device. If EN is a logic high, the device will be in shutdown mode. When EN goes to logic low, then the device will be enabled.

power-good (PG) (TPS751xxQ)

The PG terminal is an open drain, active high output that indicates the status of V_O (output of the LDO). When Vo reaches 83% of the regulated voltage, PG will go to a high impedance state. It will go to a low-impedance state when V_O falls below 83% (i.e. over load condition) of the regulated voltage. The open drain output of the PG terminal requires a pullup resistor

sense (SENSE)

The SENSE terminal of the fixed-output options must be connected to the regulator output, and the connection should be as short as possible. Internally, SENSE connects to a high-impedance wide-bandwidth amplifier through a resistor-divider network and noise pickup feeds through to the regulator output. It is essential to route the SENSE connection in such a way to minimize/avoid noise pickup. Adding RC networks between the SENSE terminal and V_{O} to filter noise is not recommended because it may cause the regulator to oscillate.

feedback (FB)

FB is an input terminal used for the adjustable-output options and must be connected to an external feedback resistor divider. The FB connection should be as short as possible. It is essential to route it in such a way to minimize/avoid noise pickup. Adding RC networks between FB terminal and Vo to filter noise is not recommended because it may cause the regulator to oscillate.

reset (RESET) (TPS753xxQ)

The RESET terminal is an open drain, active low output that indicates the status of V_O . When V_O reaches 95% of the regulated voltage, RESET will go to a low-impedance state after a 100-ms delay. RESET will go to a high-impedance state when V_{O} is below 95% of the regulated voltage. The open-drain output of the RESET terminal requires a pullup resistor.

GND/HEATSINK

All GND/HEATSINK terminals are connected directly to the mount pad for thermal-enhanced operation. These terminals could be connected to GND or left floating.

input capacitor

For a typical application, an input bypass capacitor (0.22 μ F – 1 μ F) is recommended for device stability. This capacitor should be as close to the input pins as possible. For fast transient condition where droop at the input of the LDO may occur due to high inrush current, it is recommended to place a larger capacitor at the input as well. The size of this capacitor is dependent on the output current and response time of the main power supply. as well as the distance to the load (LDO).



APPLICATION INFORMATION

output capacitor

As with most LDO regulators, the TPS751xxQ and TPS753xxQ require an output capacitor connected between OUT and GND to stabilize the internal control loop. The minimum recommended capacitance value is 47 μ F and the ESR (equivalent series resistance) must be between 100 m Ω and 10 Ω . Solid tantalum electrolytic, aluminum electrolytic, and multilayer ceramic capacitors are all suitable, provided they meet the requirements described in this section. Larger capacitors provide a wider range of stability and better load transient response.

This information, along with the ESR graphs, is included to assist in selection of suitable capacitance for the user's application. When necessary to achieve low height requirements along with high output current and/or high load capacitance, several higher ESR capacitors can be used in parallel to meet these guidelines.

ESR and transient response

LDOs typically require an external output capacitor for stability. In fast transient response applications, capacitors are used to support the load current while LDO amplifier is responding. In most applications, one capacitor is used to support both functions.

Besides its capacitance, every capacitor also contains parasitic impedances. These parasitic impedances are resistive as well as inductive. The resistive impedance is called equivalent series resistance (ESR), and the inductive impedance is called equivalent series inductance (ESL). The equivalent schematic diagram of any capacitor can therefore be drawn as shown in Figure 21.







SLVS241B - MARCH 2000 - REVISED JUNE 2003

APPLICATION INFORMATION

In most cases one can neglect the effect of inductive impedance ESL. Therefore, the following application focuses mainly on the parasitic resistance ESR.

Figure 22 shows the output capacitor and its parasitic impedances in a typical LDO output stage.

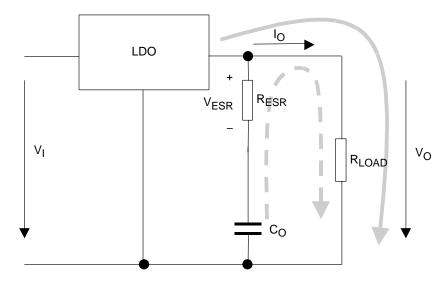


Figure 22. LDO Output Stage With Parasitic Resistances ESR and ESL

In steady state (dc state condition), the load current is supplied by the LDO (solid arrow) and the voltage across the capacitor is the same as the output voltage ($V(C_{O}) = V_{O}$). This means no current is flowing into the C_{O} branch. If In suddenly increases (transient condition), the following occurs:

- The LDO is not able to supply the sudden current need due to its response time (t₁ in Figure 23). Therefore, capacitor C_O provides the current for the new load condition (dashed arrow). C_O now acts like a battery with an internal resistance, ESR. Depending on the current demand at the output, a voltage drop will occur at RESR. This voltage is shown as VESR in Figure 22.
- When C_0 is conducting current to the load, initial voltage at the load will be $V_0 = V(C_0) V_{ESR}$. Due to the discharge of C_{O} , the output voltage V_{O} will drop continuously until the response time t₁ of the LDO is reached and the LDO will resume supplying the load. From this point, the output voltage starts rising again until it reaches the regulated voltage. This period is shown as t_2 in Figure 23.

Figure 23 also shows the impact of different ESRs on the output voltage. The left brackets show different levels of ESRs where number 1 displays the lowest and number 3 displays the highest ESR.

From above, the following conclusions can be drawn:

- The higher the ESR, the larger the droop at the beginning of load transient.
- The smaller the output capacitor, the faster the discharge time and the bigger the voltage droop during the LDO response period.



SLVS241B - MARCH 2000 - REVISED JUNE 2003

APPLICATION INFORMATION

conclusion

To minimize the transient output droop, capacitors must have a low ESR and be large enough to support the minimum output voltage requirement.

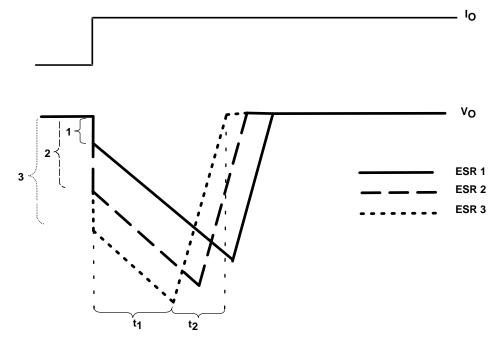


Figure 23. Correlation of Different ESRs and Their Influence to the Regulation of V_O at a Load Step From Low-to-High Output Current



SLVS241B - MARCH 2000 - REVISED JUNE 2003

APPLICATION INFORMATION

programming the TPS75x01Q adjustable LDO regulator

The output voltage of the TPS75x01Q adjustable regulator is programmed using an external resistor divider as shown in Figure 24. The output voltage is calculated using:

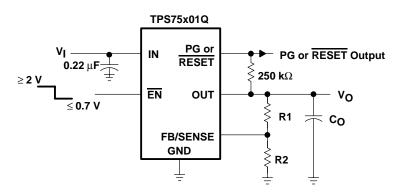
$$V_{O} = V_{ref} \times \left(1 + \frac{R1}{R2}\right)$$
(1)

Where:

V_{ref} = 1.1834 V typ (the internal reference voltage)

Resistors R1 and R2 should be chosen for approximately 40-µA divider current. Lower value resistors can be used but offer no inherent advantage and waste more power. Higher values should be avoided as leakage currents at FB increase the output voltage error. The recommended design procedure is to choose R2 = 30.1 k Ω to set the divider current at 40 μ A and then calculate R1 using:

$$R1 = \left(\frac{V_0}{V_{ref}} - 1\right) \times R2$$



OUTPUT VOLTAGE PROGRAMMING GUIDE

(2)

OUTPUT VOLTAGE	R1	R2	UNIT
2.5 V	33.2	30.1	kΩ
3.3 V	53.6	30.1	kΩ
3.6 V	61.9	30.1	kΩ

NOTE: To reduce noise and prevent oscillation, R1 and R2 need to be as close as possible to the FB/SENSE terminal.

Figure 24. TPS75x01Q Adjustable LDO Regulator Programming



APPLICATION INFORMATION

regulator protection

The TPS751xxQ or TPS753xxQ PMOS-pass transistor has a built-in back diode that conducts reverse currents when the input voltage drops below the output voltage (e.g., during power down). Current is conducted from the output to the input and is not internally limited. When extended reverse voltage is anticipated, external limiting may be appropriate.

The TPS751xxQ or TPS753xxQ also features internal current limiting and thermal protection. During normal operation, the TPS751xxQ or TPS753xxQ limits output current to approximately 3.3 A. When current limiting engages, the output voltage scales back linearly until the overcurrent condition ends. While current limiting is designed to prevent gross device failure, care should be taken not to exceed the power dissipation ratings of the package. If the temperature of the device exceeds 150°C(typ), thermal-protection circuitry shuts it down. Once the device has cooled below 130°C(typ), regulator operation resumes.

power dissipation and junction temperature

Specified regulator operation is assured to a junction temperature of 125°C; the maximum junction temperature should be restricted to 125°C under normal operating conditions. This restriction limits the power dissipation the regulator can handle in any given application. To ensure the junction temperature is within acceptable limits, calculate the maximum allowable dissipation, $P_{D(max)}$, and the actual dissipation, P_{D} , which must be less than or equal to $P_{D(max)}$.

The maximum-power-dissipation limit is determined using the following equation:

$$P_{D(max)} = \frac{T_{J}max - T_{A}}{R_{\theta JA}}$$
(3)

Where:

T_Jmax is the maximum allowable junction temperature

 $R_{\theta JA}$ is the thermal resistance junction-to-ambient for the package, i.e., 34.6°C/W for the 20-terminal PWP with no airflow (see Table 1).

T_A is the ambient temperature.

The regulator dissipation is calculated using:

$$\mathsf{P}_{\mathsf{D}} = \left(\mathsf{V}_{\mathsf{I}} - \mathsf{V}_{\mathsf{O}}\right) \times \mathsf{I}_{\mathsf{O}} \tag{4}$$

Power dissipation resulting from quiescent current is negligible. Excessive power dissipation will trigger the thermal protection circuit.



SLVS241B - MARCH 2000 - REVISED JUNE 2003

THERMAL INFORMATION

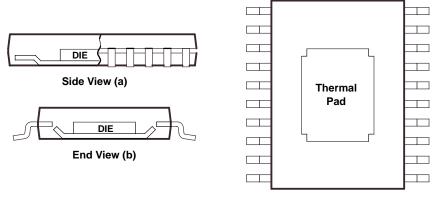
thermally enhanced TSSOP-20 (PWP – PowerPad™)

The thermally enhanced PWP package is based on the 20-pin TSSOP, but includes a thermal pad [see Figure 25(c)] to provide an effective thermal contact between the IC and the PWB.

Traditionally, surface mount and power have been mutually exclusive terms. A variety of scaled-down TO220-type packages have leads formed as gull wings to make them applicable for surface-mount applications. These packages, however, suffer from several shortcomings: they do not address the very low profile requirements (<2 mm) of many of today's advanced systems, and they do not offer a pin-count high enough to accommodate increasing integration. On the other hand, traditional low-power surface-mount packages require power-dissipation derating that severely limits the usable range of many high-performance analog circuits.

The PWP package (thermally enhanced TSSOP) combines fine-pitch surface-mount technology with thermal performance comparable to much larger power packages.

The PWP package is designed to optimize the heat transfer to the PWB. Because of the very small size and limited mass of a TSSOP package, thermal enhancement is achieved by improving the thermal conduction paths that remove heat from the component. The thermal pad is formed using a lead-frame design (patent pending) and manufacturing technique to provide the user with direct connection to the heat-generating IC. When this pad is soldered or otherwise coupled to an external heat dissipator, high power dissipation in the ultrathin, fine-pitch, surface-mount package can be reliably achieved.



Bottom View (c)

Figure 25. Views of Thermally Enhanced PWP Package

Because the conduction path has been enhanced, power-dissipation capability is determined by the thermal considerations in the PWB design. For example, simply adding a localized copper plane (heat-sink surface), which is coupled to the thermal pad, enables the PWP package to dissipate 2.5 W in free air (reference Figure 27(a), 8 cm² of copper heat sink and natural convection). Increasing the heat-sink size increases the power dissipation range for the component. The power dissipation limit can be further improved by adding airflow to a PWB/IC assembly (see Figures 26 and 27). The line drawn at 0.3 cm² in Figures 26 and 27 indicates performance at the minimum recommended heat-sink size, illustrated in Figure 29.

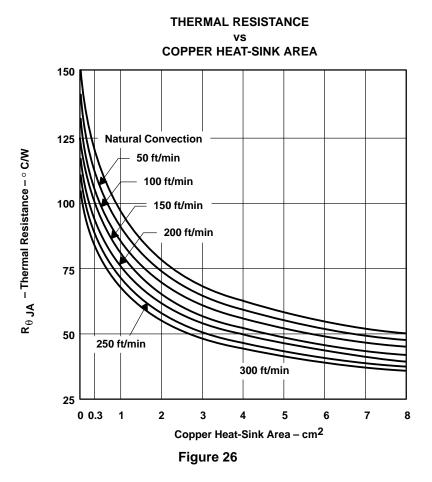


SLVS241B - MARCH 2000 - REVISED JUNE 2003

THERMAL INFORMATION

thermally enhanced TSSOP-20 (PWP – PowerPad[™]) (continued)

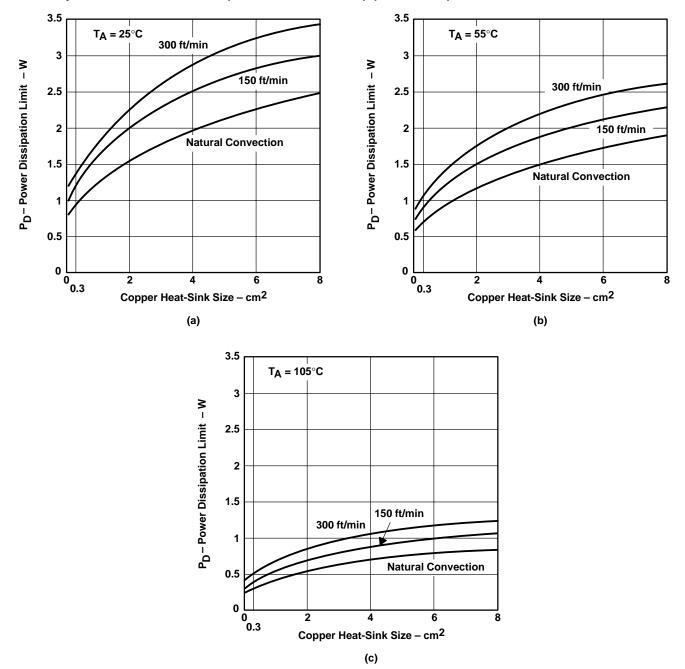
The thermal pad is directly connected to the substrate of the IC, which for the TPS751xxQPWP and TPS753XXQPWP series is a secondary electrical connection to device ground. The heat-sink surface that is added to the PWP can be a ground plane or left electrically isolated. In TO220-type surface-mount packages, the thermal connection is also the primary electrical connection for a given terminal which is not always ground. The PWP package provides up to 16 independent leads that can be used as inputs and outputs (Note: leads 1, 10, 11, and 20 are internally connected to the thermal pad and the IC substrate).





SLVS241B - MARCH 2000 - REVISED JUNE 2003

THERMAL INFORMATION



thermally enhanced TSSOP-20 (PWP – PowerPad[™]) (continued)

Figure 27. Power Ratings of the PWP Package at Ambient Temperatures of 25°C, 55°C, and 105°C

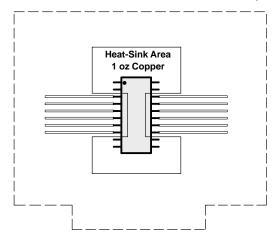


SLVS241B - MARCH 2000 - REVISED JUNE 2003

THERMAL INFORMATION

thermally enhanced TSSOP-20 (PWP – PowerPad[™]) (continued)

Figure 28 is an example of a thermally enhanced PWB layout for use with the new PWP package. This board configuration was used in the thermal experiments that generated the power ratings shown in Figure 26 and Figure 27. As discussed earlier, copper has been added on the PWB to conduct heat away from the device. $R_{\theta,IA}$ for this assembly is illustrated in Figure 26 as a function of heat-sink area. A family of curves is included to illustrate the effect of airflow introduced into the system.



Board thickness	62 mils
Board size	3.2 in. \times 3.2 in.
Board material	FR4
Copper trace/heat sink	1 oz
Exposed pad mounting	63/67 tin/lead solder

Figure 28. PWB Layout (Including Copper Heatsink Area) for Thermally Enhanced PWP Package

From Figure 26, R_{0.1A} for a PWB assembly can be determined and used to calculate the maximum power-dissipation limit for the component/PWB assembly, with the equation:

$$P_{D(max)} = \frac{T_{J}max - T_{A}}{R_{\theta JA(system)}}$$
(5)

Where:

T₁max is the maximum specified junction temperature (150°C absolute maximum limit, 125°C recommended operating limit) and T_A is the ambient temperature.

P_{D(max)} should then be applied to the internal power dissipated by the TPS75133QPWP regulator. The equation for calculating total internal power dissipation of the TPS75133QPWP is:

$$\mathsf{P}_{\mathsf{D}(\mathsf{total})} = \left(\mathsf{V}_{\mathsf{I}} - \mathsf{V}_{\mathsf{O}}\right) \times \mathsf{I}_{\mathsf{O}} + \mathsf{V}_{\mathsf{I}} \times \mathsf{I}_{\mathsf{Q}}$$
(6)

Since the quiescent current of the TPS75133QPWP is very low, the second term is negligible, further simplifying the equation to:

$$\mathsf{P}_{\mathsf{D}(\mathsf{total})} = \left(\mathsf{V}_{\mathsf{I}} - \mathsf{V}_{\mathsf{O}}\right) \times \mathsf{I}_{\mathsf{O}} \tag{7}$$

For the case where $T_A = 55^{\circ}C$, airflow = 200 ft/min, copper heat-sink area = 4 cm², the maximum power-dissipation limit can be calculated. First, from Figure 26, we find the system R_{0JA} is 50°C/W; therefore, the maximum power-dissipation limit is:

$$P_{D(max)} = \frac{T_J max - T_A}{R_{\theta JA(system)}} = \frac{125 \,^{\circ}\text{C} - 55 \,^{\circ}\text{C}}{50 \,^{\circ}\text{C/W}} = 1.4 \text{ W}$$
(8)



SLVS241B - MARCH 2000 - REVISED JUNE 2003

THERMAL INFORMATION

thermally enhanced TSSOP-20 (PWP – PowerPad[™]) (continued)

If the system implements a TPS75133QPWP regulator, where $V_1 = 5$ V and $I_0 = 800$ mA, the internal power dissipation is:

$$P_{D(total)} = (V_{I} - V_{O}) \times I_{O} = (5 - 3.3) \times 0.8 = 1.36 \text{ W}$$
 (9)

Comparing PD(total) with PD(max) reveals that the power dissipation in this example does not exceed the calculated limit. When it does, one of two corrective actions should be made: raising the power-dissipation limit by increasing the airflow or the heat-sink area, or lowering the internal power dissipation of the regulator by reducing the input voltage or the load current. In either case, the above calculations should be repeated with the new system parameters.

mounting information

The primary requirement is to complete the thermal contact between the thermal pad and the PWB metal. The thermal pad is a solderable surface and is fully intended to be soldered at the time the component is mounted. Although voiding in the thermal-pad solder-connection is not desirable, up to 50% voiding is acceptable. The data included in Figures 26 and 27 is for soldered connections with voiding between 20% and 50%. The thermal analysis shows no significant difference resulting from the variation in voiding percentage.

Figure 29 shows the solder-mask land pattern for the PWP package. The minimum recommended heat-sink area is also illustrated. This is simply a copper plane under the body extent of the package, including metal routed under terminals 1, 10, 11, and 20.

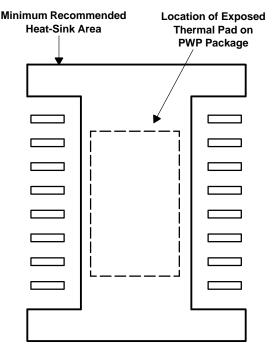


Figure 29. PWP Package Land Pattern



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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPS75101QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75101QPWPG4	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75101QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75101QPWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75115QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75115QPWPG4	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75115QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75115QPWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75118QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75118QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75125QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75125QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75125QPWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75133QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75133QPWPG4	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75133QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75133QPWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75301QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75301QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75301QPWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75315QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75315QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75315QPWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75318QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75318QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPS75318QPWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75325QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75325QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75325QPWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75333QPWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75333QPWPG4	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75333QPWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS75333QPWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

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OBSOLETE: TI has discontinued the production of the device.

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⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com http://www.ti.com.
- E. Falls within JEDEC MO-153

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